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Team Nexperia



PMZ1000UN

N-channel TrenchMOS standard level FET

Rev. 2 — 17 September 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Fast switching
- Low conduction losses due to low on-state resistance
- Saves PCB space due to small footprint (90 % smaller than SOT23)
- Suitable for use in compact designs due to low profile (55 % lower than SOT23)

1.3 Applications

Driver circuits

Switching in portable appliances

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C \leq T $_{j}$ \leq 150 °C	-	-	30	V
I _D	drain current	$T_{amb} = 25 ^{\circ}C; V_{GS} = 10 V;$ see Figure 1	-	-	480	mA
P _{tot}	total power dissipation	$T_{amb} = 25 ^{\circ}C$; see Figure 2	-	-	350	mW
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 0.2 \text{ A};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	1	Ω



2. Pinning information

Table 2. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source	1 3	D D
3	D	drain	2	
			Transparent top view	
			SOT883 (SC-101)	mbb076 S

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMZ1000UN	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883			

4. Marking

Table 4. Marking codes

Type number	Marking code
PMZ1000UN	6N

5. Limiting values

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C	-	30	V
V_{DGR}	drain-gate voltage	$25 ^{\circ}\text{C} \le \text{T}_{j} \le 150 ^{\circ}\text{C}; \text{R}_{\text{GS}} = 20 \text{k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-8	+8	V
I _D	drain current	T_{amb} = 25 °C; V_{GS} = 10 V; see Figure 1	-	480	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; $t_p \le 10 \mu s$; pulsed	-	1.8	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; see <u>Figure 2</u>	-	350	mW
T _{stg}	storage temperature		-55	+150	°C
Tj	junction temperature		-55	+150	°C

PMZ1000UN

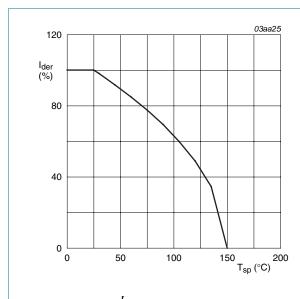
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 Table 5.
 Limiting values ...continued

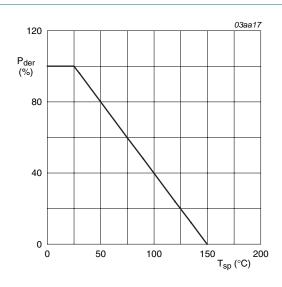
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbo	I Parameter	Conditions	Min	Max	Unit
Source	-drain diode				
Is	source current	T _{amb} = 25 °C	-	480	mA
Electro	static discharge				
V_{ESD}	electrostatic discharge voltage	HBM; C = 100 pF; R = 1.5 kΩ	-	60	V
		MM; C = 200 pF	-	30	V



 $I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$

Fig 1. Normalized continuous drain current as a function of solder point temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

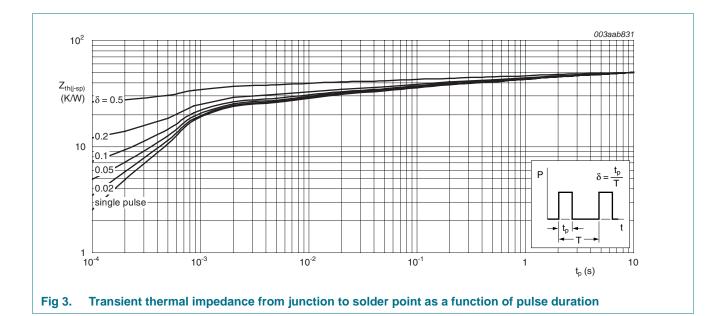
Fig 2. Normalized total power dissipation as a function of solder point temperature

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	see Figure 3	-	-	50	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		[1] -	-	355	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

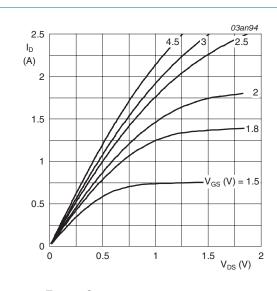


7. Characteristics

Table 7. Characteristics

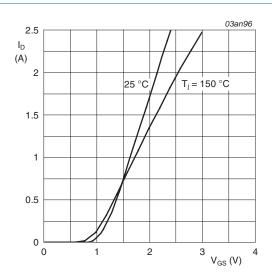
 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 10 \mu A; V_{GS} = 0 V$				
	voltage	T _j = 25 °C	30	-	-	V
		T _j = −55 °C	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 0.25 \text{ mA}$; $V_{DS} = V_{GS}$; see Figure 6 and 7				
		T _j = 25 °C	0.45	0.7	0.95	V
		T _j = 150 °C	0.25	-	-	V
		T _j = −55 °C	-	-	1.15	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μΑ
		T _j = 150 °C	-	-	100	μΑ
I_{GSS}	gate leakage current	$V_{GS} = \pm 8 \text{ V}; V_{DS} = 0 \text{ V}$	-	10	100	nΑ
R_{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}$; $I_D = 0.2 \text{ A}$; see Figure 8				
	resistance	T _j = 25 °C	-	-	1	Ω
		T _j = 150 °C	-	-	1.5	Ω
		V _{GS} = 2.5 V; I _D = 0.1 A; <u>Figure 8</u>	-	-	1.1	Ω
		V _{GS} = 1.8 V; I _D = 0.075 A; <u>Figure 8</u>	-	-	1.4	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 1 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	0.89	-	nC
Q_{GS}	gate-source charge	see Figure 9 and 10	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	43	-	pF
C _{oss}	output capacitance	see Figure 11	-	7.7	-	pF
C _{rss}	reverse transfer capacitance		-	4.8	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_L = 15 Ω ; V_{GS} = 10 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$	-	7.5	-	ns
t _{d(off)}	turn-off delay time		-	18	-	ns
t _f	fall time		-	4.5	-	ns
Source-	drain diode					
V_{SD}	source-drain voltage	$I_S = 0.3 \text{ A}$; $V_{GS} = 0 \text{ V}$; see Figure 11	-	0.76	1.2	V



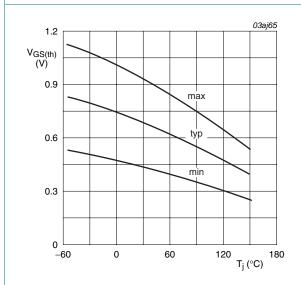
 $T_j = 25 \, ^{\circ}C$

Fig 4. Output characteristics: drain current as a function of drain-source voltage; typical values



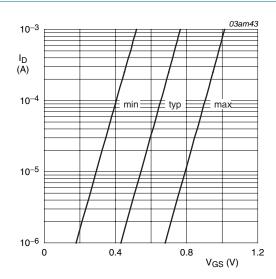
 T_{j} = 25 °C and 150 °C; V_{DS} > $I_{D} \times R_{DSon}$

Fig 5. Transfer characteristics: drain current as a function of gate-source voltage; typical values



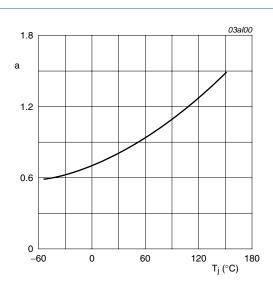
 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 6. Gate-source threshold voltage as a function of junction temperature



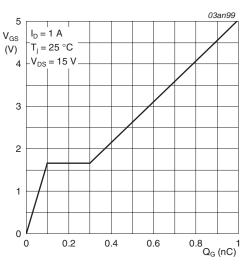
 $T_i = 25 \,^{\circ}C; V_{DS} = 5 \,^{\circ}V$

Fig 7. Sub-threshold drain current as a function of gate-source voltage



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

Fig 8. Normalized drain-source on-state resistance as a function of junction temperature



$$I_D = 1 A; V_{DS} = 15 V$$

Fig 9. Gate-source voltage as a function of gate charge; typical values

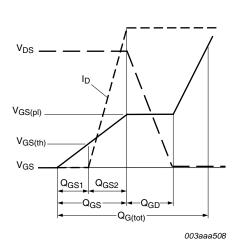
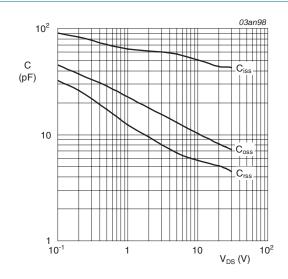
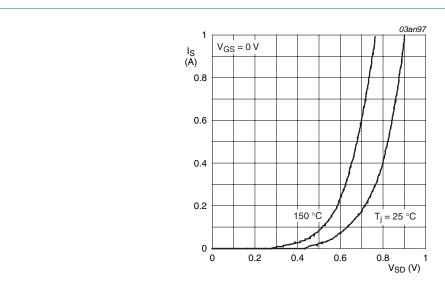


Fig 10. Gate charge waveform definitions



 $V_{GS} = 0 V$; f = 1 MHz

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 T_{j} = 25 °C and 150 °C; V_{GS} = 0 V

Fig 12. Source current as a function of source-drain voltage; typical values

8. Package outline

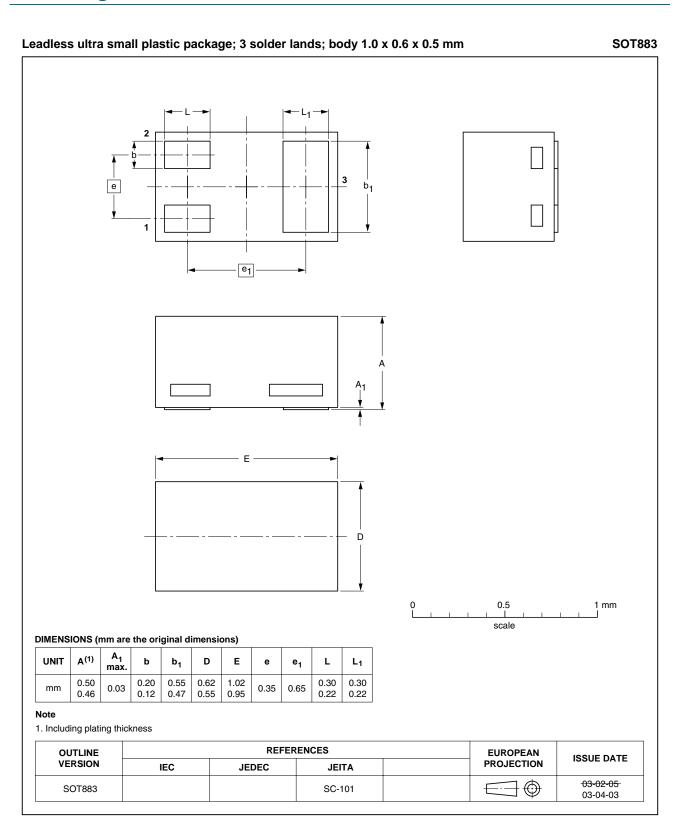


Fig 13. Package outline SO883 (SC-101)

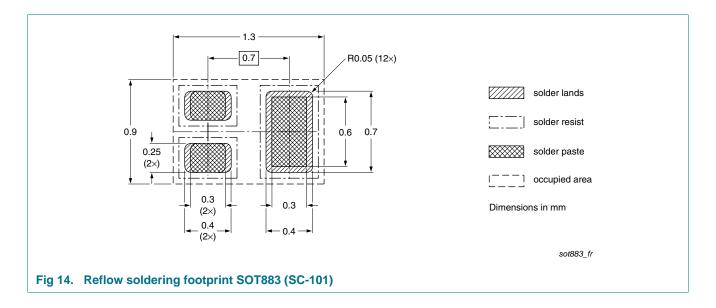
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9. Soldering



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10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMZ1000UN v.2	20100917	Product data sheet	-	PMZ1000UN_1
Modifications:	 Modification 	ns of thermal parameters		
	Section 11	"Legal information": updated		
PMZ1000UN_1	20100224	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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